

Chao-Hui Yeh

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6910902/publications.pdf>

Version: 2024-02-01

43
papers

3,405
citations

218381

26
h-index

288905

40
g-index

44
all docs

44
docs citations

44
times ranked

6859
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 1 | Graphene Annealing: How Clean Can It Be?. Nano Letters, 2012, 12, 414-419. | 4.5 | 801 |
| 2 | Single-Layer ReS ₂ : Two-Dimensional Semiconductor with Tunable In-Plane Anisotropy. ACS Nano, 2015, 9, 11249-11257. | 7.3 | 353 |
| 3 | Structural and Chemical Dynamics of Pyridinic-Nitrogen Defects in Graphene. Nano Letters, 2015, 15, 7408-7413. | 4.5 | 204 |
| 4 | Three-fold rotational defects in two-dimensional transition metal dichalcogenides. Nature Communications, 2015, 6, 6736. | 5.8 | 179 |
| 5 | Twisting Bilayer Graphene Superlattices. ACS Nano, 2013, 7, 2587-2594. | 7.3 | 173 |
| 6 | High Mobility Flexible Graphene Field-Effect Transistors with Self-Healing Gate Dielectrics. ACS Nano, 2012, 6, 4469-4474. | 7.3 | 169 |
| 7 | Metal-Free Growth of Nanographene on Silicon Oxides for Transparent Conducting Applications. Advanced Functional Materials, 2012, 22, 2123-2128. | 7.8 | 150 |
| 8 | Remote Catalyzation for Direct Formation of Graphene Layers on Oxides. Nano Letters, 2012, 12, 1379-1384. | 4.5 | 146 |
| 9 | Magnetotransport at Domain Walls in BiFeO_3 . Physical Review Letters, 2012, 108, 067203. | 2.9 | 131 |
| 10 | Gigahertz Flexible Graphene Transistors for Microwave Integrated Circuits. ACS Nano, 2014, 8, 7663-7670. | 7.3 | 92 |
| 11 | Ferroelectric Control of the Conduction at the LaAlO ₃ /SrTiO ₃ Heterointerface. Advanced Materials, 2013, 25, 3357-3364. | 11.1 | 90 |
| 12 | Stable 1T Tungsten Disulfide Monolayer and Its Junctions: Growth and Atomic Structures. ACS Nano, 2018, 12, 12080-12088. | 7.3 | 74 |
| 13 | Robust room temperature valley polarization in monolayer and bilayer WS ₂ . Nanoscale, 2016, 8, 6035-6042. | 2.8 | 68 |
| 14 | Growth and Raman Spectra of Single-Crystal Trilayer Graphene with Different Stacking Orientations. ACS Nano, 2014, 8, 10766-10773. | 7.3 | 56 |
| 15 | In situ observation of step-edge in-plane growth of graphene in a STEM. Nature Communications, 2014, 5, 4055. | 5.8 | 55 |
| 16 | In Situ Tuning of Switching Window in a Gate-Controlled Bilayer Graphene Electrode Resistive Memory Device. Advanced Materials, 2015, 27, 7767-7774. | 11.1 | 54 |
| 17 | Graphene Transition Metal Dichalcogenide Heterojunctions for Scalable and Low-Power Complementary Integrated Circuits. ACS Nano, 2020, 14, 985-992. | 7.3 | 46 |
| 18 | End-Bonded Metal Contacts on WS ₂ Field-Effect Transistors. ACS Nano, 2019, 13, 8146-8154. | 7.3 | 44 |

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 37 | Demonstration of CMOS-Compatible Multi-Level Graphene Interconnects With Metal Vias. IEEE Transactions on Electron Devices, 2021, 68, 2083-2091. | 1.6 | 10 |
| 38 | Impact of Transport Anisotropy on the Performance of van der Waals Materials-Based Electron Devices. IEEE Transactions on Electron Devices, 2020, 67, 1310-1316. | 1.6 | 8 |
| 39 | Two-dimensional materials enabled next-generation low-energy compute and connectivity. MRS Bulletin, 2021, 46, 1211-1228. | 1.7 | 8 |
| 40 | Characterization of Graphene and Transition Metal Dichalcogenide at the Atomic Scale. Journal of the Physical Society of Japan, 2015, 84, 121005. | 0.7 | 6 |
| 41 | 0.5T0.5R - Introducing an Ultra-Compact Memory Cell Enabled by Shared Graphene Edge-Contact and h-BN Insulator. , 2020, , . | | 3 |
| 42 | Memory Devices: In Situ Tuning of Switching Window in a Gate-Controlled Bilayer Graphene-Electrode Resistive Memory Device (Adv. Mater. 47/2015). Advanced Materials, 2015, 27, 7766-7766. | 11.1 | 1 |
| 43 | Reliability and Performance of CMOS-Compatible Multi-Level Graphene Interconnects Incorporating Vias. , 2020, , . | | 0 |